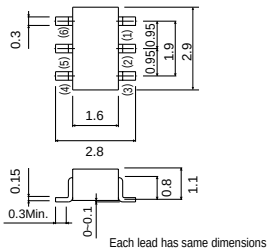
General purpose (dual transistors)

IMX8

●Features

1) Two 2SC3906K chips in an SMT package.
2) High breakdown voltage.

●External dimensions (Units : mm)



ROHM : SMT6
EIAJ : SC-74

●Absolute maximum ratings (Ta=25°C)

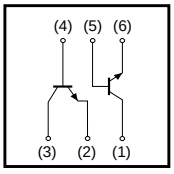
Parameter	Symbol	Limits	Unit	
Collector-base voltage	V_{CBO}	120	V	
Collector-emitter voltage	V_{CEO}	120	V	
Emitter-base voltage	V_{EBO}	5	V	
Collector current	I_C	50	mA	
Power dissipation	Pc	300(TOTAL)	mW	✻
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	−55~+150	°C	

✻ 200mW per element must not be exceeded.

●Package, marking, and packaging specifications

Part No.	IMX8
Package	SMT6
Marking	X4
Code	T108
Basic ordering unit (pieces)	3000

●Equivalent circuit



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	120	–	–	V	I_C=50μA
Collector-emitter breakdown voltage	BV_{CEO}	120	–	–	V	I_C=1mA
Emitter-base breakdown voltage	BV_{EBO}	5	–	–	V	I_E=50μA
Collector cutoff current	I_{CBO}	–	–	0.5	μA	V_{CB}=100V
Emitter cutoff current	I_{EBO}	–	–	0.5	μA	V_{EB}=4V
DC current transfer ratio	h_{FE}	180	–	820	–	V_{CE}=6V, I_C=2mA
Transition frequency	f_T	–	140	–	MHz	V_{CE}=−12V, I_E=2mA, f=100MHz ✻
Collector-emitter saturation voltage	$V_{CE(sat)}$	–	–	0.5	V	I_C/I_B=10mA/1mA

✻Transition frequency of the device